PRELIMINARY SPECIFICATION

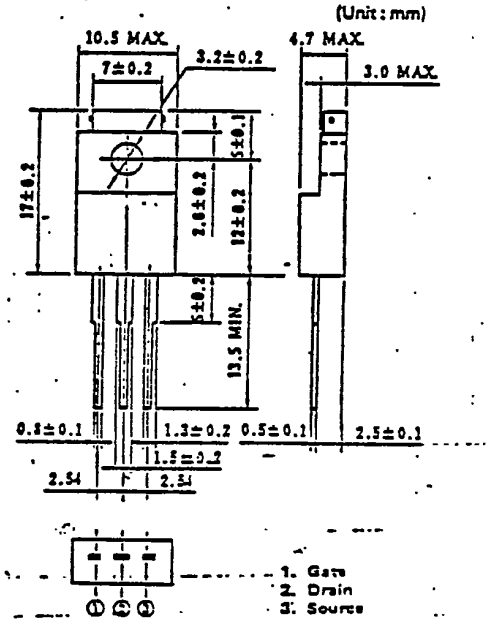
NEC ELECTRON DEVICE

MOS FIELD EFFECT TRANSISTOR

2SJ135

FAST SWITCHING P-CHANNEL SILICON POWER MOS FET

PACKAGE DIMENSIONS (Unit: mm)



Features

Suitable for switching power supplies, actuator controls and pulse circuits
4V Gate Drive —— Logic Level ——
Large current switching : ID(DC)= 5A
Low RDS(on)
No Secondary Breakdown

Absolute Maximum Ratings(Ta=25℃)

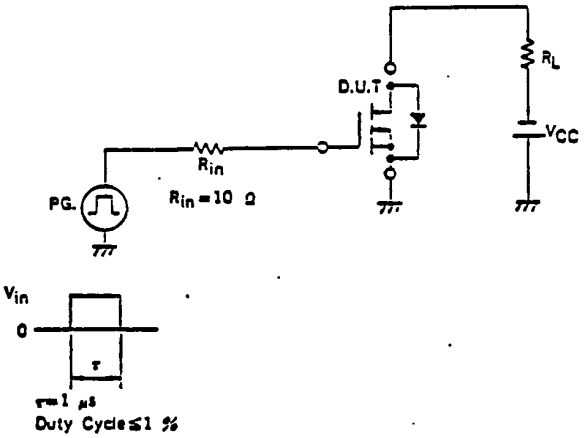
Drain to Source Voltage	VDSS	-100V
Gate to Source Voltage	VGSS	± 20V
Continuous Drain Current	ID(DC)	±5.0A
Pulse Drain Current	ID(pulse)	*± 20A
Total Power Dissipation	PT	2.0W
Total Power Dissipation	PT**	30W
Channel Temperature	Tch	150 ℃
Storage Temperature	Tstg	-55to+150 ℃

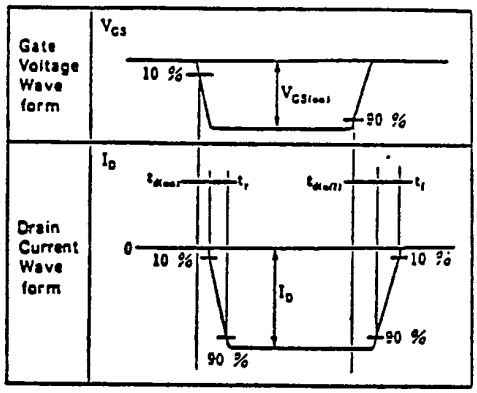
* Tch ≦ 150℃
** Tc=25 ℃

Electrical Characteristics (Ta=25 ℃)

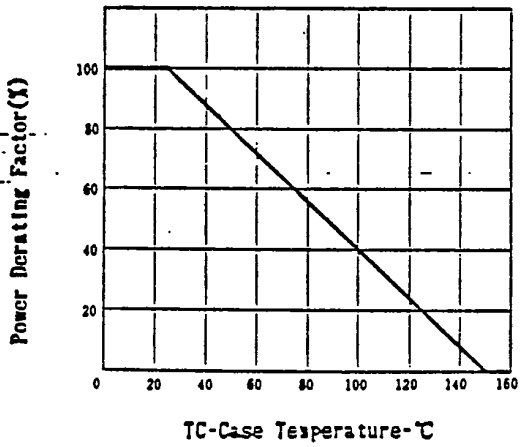
Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain Leakage Current	IDSS			- 10	μA	VDS=-100V,VGS=0
Gate to Source Leakage Current	IGSS			100	nA	VGS= 20V,VDS=0
Gate to Source Cutoff Voltage	VGS(off)	-1.0		-3.0	V	VDS=-10V,ID=-1.0mA
Forward Transfer Admittance	|yfs|	1.0			S	VDS=-10V,ID=-3.5A
Drain to Source On-State Resistance	RDS(on)			0.6	Ω	VGS=-10V,ID=-3.5A
Drain to Source On-State Resistance	RDS(on)			0.9	Ω	VGS=-4.0V,ID=-3.5A
Input Capacitance	Ciss		1600		pF	VDS=-10V,
Output Capacitance	Coss		400		pF	VGS=0,
Reverse Transfer Capacitance	Crss		65		pF	f=1.0MHz
Turn-On Delay Time	td(on)		9		ns	ID=-3.5A,
Rise Time	tr		35		ns	VGS(on)=-10V,
Turn-Off Delay Time	td(off)		55		ns	Vcc=-50V,
Fall Time	tf		40		ns	RL=15 Ω

TURN-ON AND TURN-OFF TIME TEST CIRCUIT

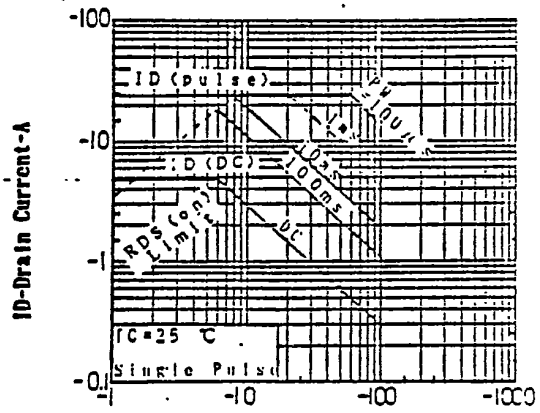




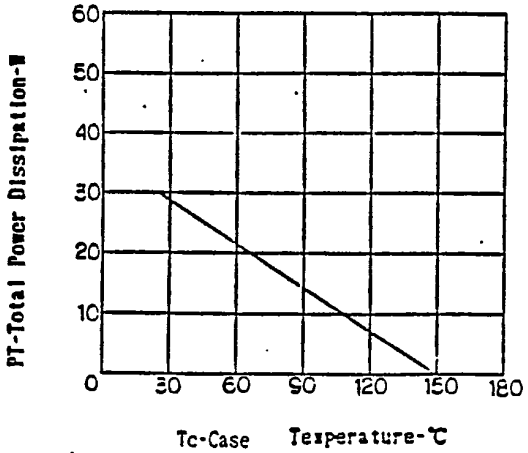
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



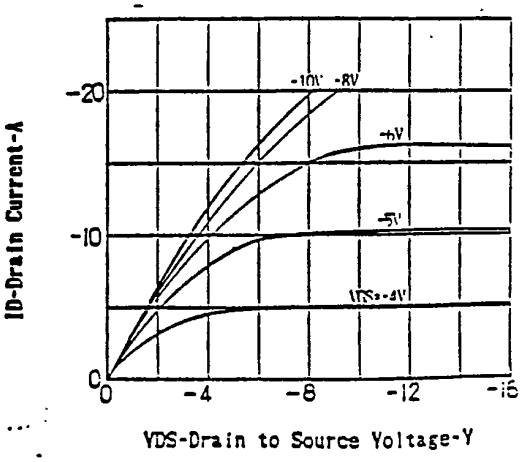
FORWARD BIAS SAFE OPERATING AREA



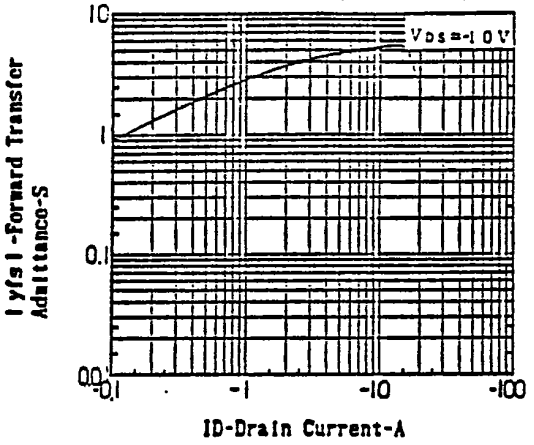
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



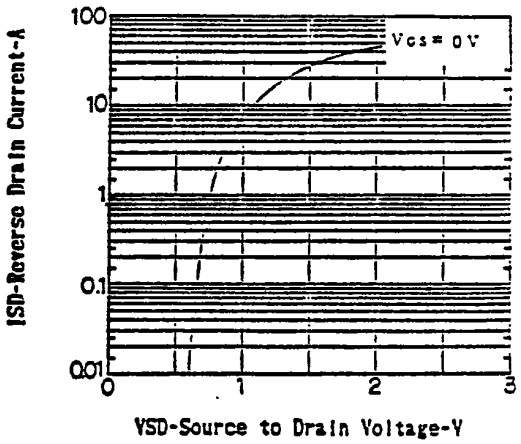
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



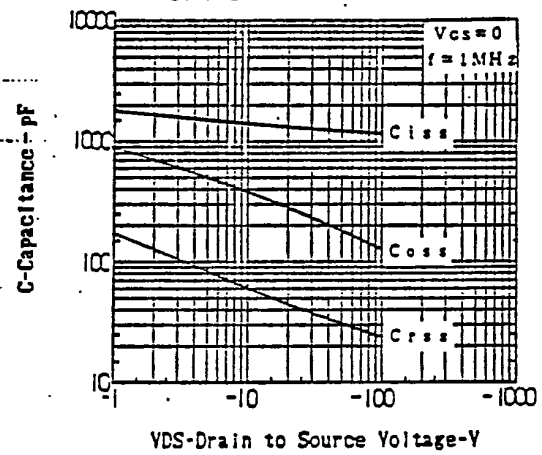
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



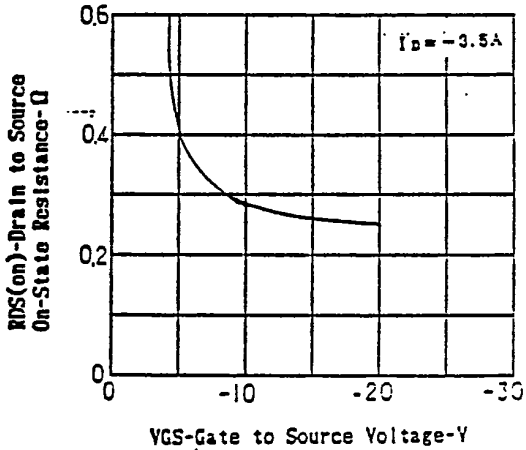
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



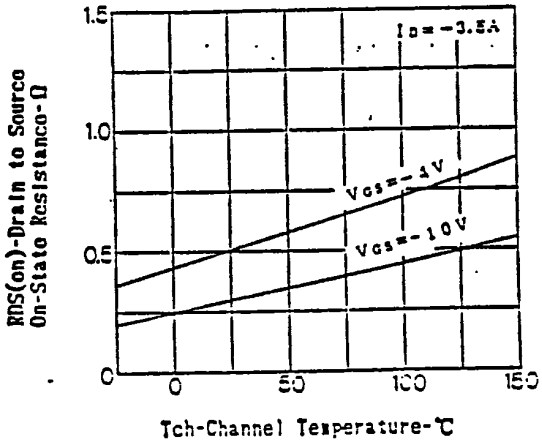
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



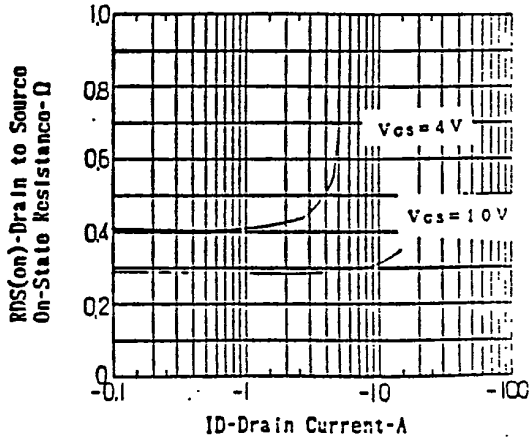
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



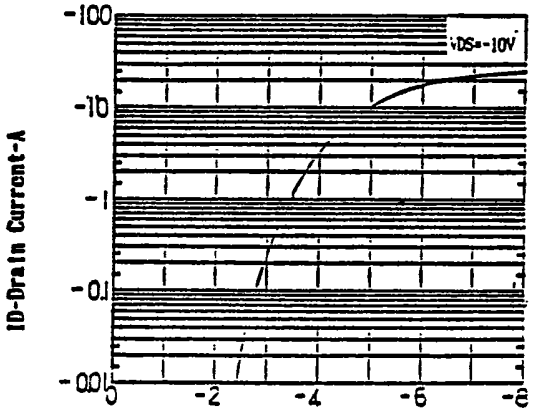
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



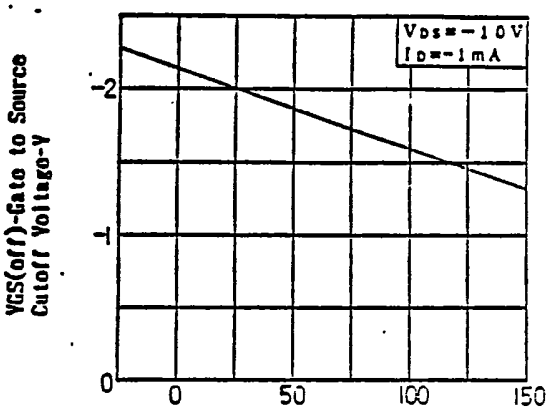
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



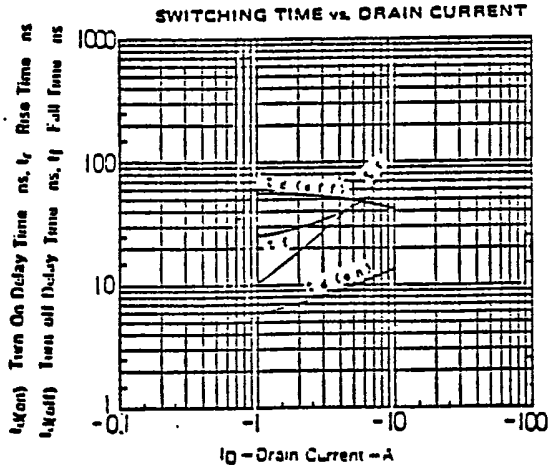
TRANSFER CHARACTERISTICS



GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



SWITCHING TIME vs. DRAIN CURRENT



NEC Corporation
INTERNATIONAL ELECTRON DEVICES DIV.
NEC Building, 33-1, Shiba Gochome
Minato-ku, Tokyo 108, Japan
Tel: Tokyo 454-1111
Telex Address: NECTOK J22686
Cable Address: MICROPHONE TOKYO

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